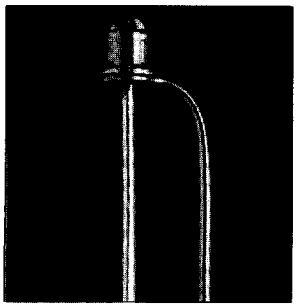
.025" NPN Phototransistors
Hermetic Coax Package w/ Emitter Lead

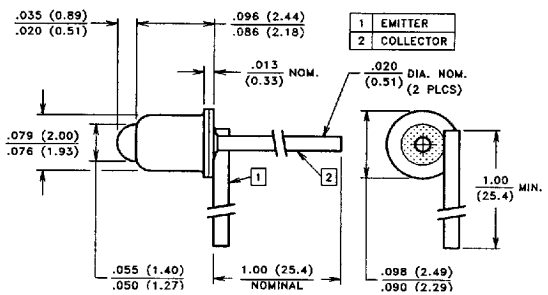
VTT3121E, 2E, 3E

E G & G VACTEC

T-41-61



PACKAGE DIMENSIONS inch (mm)



CASE 5 COAX HERMETIC (WITH CASE LEAD)
CHIP TYPE: 25T

PRODUCT DESCRIPTION

A small area high speed NPN silicon phototransistor in a lensed, hermetic glass to metal sealed, subminiature package. The package design is ideally suited for mounting into P.C. board. The lead welded to the case provides contact to the emitter. These devices are spectrally and mechanically matched to the VTE31xx series of IREDs.

ABSOLUTE MAXIMUM RATINGS ■
(@ 25°C unless otherwise noted)

Maximum Temperatures
Storage Temperature: -55°C to 125°C
Operating Temperature: -40°C to 125°C

Continuous Power Dissipation: 50 mW
Derate above 30°C: 0.53 mW/ °C

Maximum Current: 25 mA

Lead Soldering Temperature: 260°C
(1.6 mm from case, 5 sec. max.)

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also 25T curves, pg. 15 & 16)

Part Number	Light Current			Dark Current		Collector Breakdown	Emitter Breakdown	Saturation Voltage	Rise / Fall Time	Angular Response
	I_C			I_{CEO}		$V_{BR(CEO)}$	$V_{BR(ECO)}$	$V_{CE(SAT)}$	t_R / t_F	$\theta_{1/2}$
	mA		H fc (mW/cm^2) V_{CE} = 5.0 V	H=0		I_C =100 μA H=0	I_E =100 μA H=0	I_C =1.0 mA H=400 fc	I_C =1.0 mA R_L=100 Ω	
	Min.	Max.		(nA) Max.	V_{CE} (Volts)	Volts, Min.	Volts, Min.	Volts, Max.	μsec, Typ.	Typ.
VTT3121E	0.5	1.5	100 (5)	100	20	50	6.0	0.25	1.5	±8°
VTT3122E	1.2	5.0	100 (5)	100	20	40	6.0	0.25	2.5	±8°
VTT3123E	4.0	—	100 (5)	100	10	30	4.0	0.25	4.0	±8°